



<b>Form 1449 (Modified)</b>		<b>Atty Docket No.</b>	NOVLP094/NVLS-2919
<b>Information Disclosure Statement By Applicant</b>		<b>Application No.:</b>	10/789,103
		<b>Applicant</b>	Wu et al.
		<b>Filing Date</b>	February 27, 2004
		<b>Group</b>	1762
		Page 1 of 1	
(Use Several Sheets if Necessary)			

**U.S. Patent Documents**

<b>Examiner Initial</b>	<b>No.</b>	<b>Patent No.</b>	<b>Date</b>	<b>Patentee</b>	<b>Class</b>	<b>Sub-class</b>	<b>Filing Date</b>
	1.	7,166,531	01.2007	van den Hoek et al.			
	2.	7,176,144	02.2007	Wang et al.			
	3.	6,268,288 B1	07.2001	Hautala et al.			
	4.	6,759,098 B2	07.2004	Han et al.			
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	7.	2002/0172766 A1	11.2002	Laxman et al.			
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	9.	6,921,727 B2	07.2005	Chiang et al.			
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	11.	2005/0156285 A1	07.2005	Gates et al.			
	12.	7,064,088 B2	06.2006	Hyodo et al.			
	13.	7,241,704 B1	07.10.07	Wu et al.			

**Other Documents**

<b>Examiner Initial</b>	<b>No.</b>	<b>Author, Title, Place (e.g. Journal) of Publication, Date</b>
	14.	U.S. Office Action dated November 28, 2007, from U.S. Application No. 10/807,680 [Atty Dkt: NOVLP97/NVLS-2906]
	15.	R.J. Lewis, Sr., Hawley's Condensed Chemical Dictionary, 12 <sup>th</sup> Edition, Van Nostrand Reinhold Co., New York, 1993 (no month), excerpts pages 916-918 & 1123-1124.
	16.	Wu et al., "Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups", U.S. Application No. 11/764,750, filed June 18, 2007 [Atty Dkt: NOVLP106D1/NVLS-2930D1]
	17.	Wu et al., "Methods For Producing Low-K CDO Films," U.S. Application No. 11/936,754, filed November 7, 2007 [Atty Docket No.: NOVLP098D1/NVLS-2907D1]
	18.	Wu et al., "Methods For Improving Integration Performance of Low Stress CDO Films", U.S. Application No. 11/936,752, filed November 7, 2007 [Atty Dkt: NOVLP107D1/NVLS-2932D1]
	19.	U.S. Notice of Allowance and Fee Due mailed September 27, 2007, from U.S. Application No. 11/376,510. [NOVLP099D1/NVLS-2896D1]
	20.	Allowed Claims from U.S. Application No. 11/376,510. [NOVLP099D1/NVLS-2896D1]

<b>Examiner</b>	<b>Date Considered</b>
/Bret Chen/	02/27/2008

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

**ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BC/**